Amendments to the Specification:

Please replace the paragraph beginning at page 1, line 9 with the following amended paragraph:

U.S. Serial Number.10/242,266, entitled "ENCAPSULATION FOR ORGANIC DEVICES" by Hagen Klausmann, Yuen Sin Lew, Hou Siong Tan and Hooi Bin Lim, filed September 12, 2002~~(attorney docket: 2002P13935US)~~; U.S. Serial Number 10/242,068, filed September 11, 2002, entitled "METHOD OF FABRICATING ELECTRONIC DEVICES" by Hagen Klausmann and Bernd Fritz ~~(attorney docket: 2002P13934US)~~; and U.S. Ser. No. 10/242,656, filed September 12, 2202, entitled "ACTIVE ELECTRONIC DEVICES" by Reza Stegamat ~~(attorney docket: 2002P03163US)~~. All of these applications are incorporated by reference herein in their entirety.

Please replace the paragraph beginning at page 9, line 14 with the following amended paragraph:

In one embodiment, the cap is mounted onto a bonding region of the substrate. In one embodiment, a protective layer can be provided in the bonding region to protect the layers beneath. In a preferred embodiment, the protective layer comprises an insulating material. The use of an insulating material is useful to prevent shorting of conducting lines which provide electrical access to the device. For some applications, a dielectric protective layer may be required in the bonding region to prevent conductive lines on the substrate in the bonding region from being shorted when a conductive cap or conductive post is used. The protective layer comprises, for example, photoresist or photosensitive polyimide. The use of protective layer in the bonding region is described in copending patent application "Improved Encapsulation for Electroluminescent Devices", USSN 10/142,208 ~~(attorney docket number 12205/16)~~ filed on May 7, 2002, which is herein incorporated by reference for all purposes. Alternatively, other dielectric materials, such as silicon oxide, silicate glass, or silicon nitride, are also useful. If an insulating material is not required, a conductive material can be used to form the protective layer.

Please replace the paragraph on page 10, line 19 with the following amended paragraph:

The getter material can be deposited using various techniques. In one embodiment, the getter material is deposited by evaporation, such as thermal or electron beam. Sputtering techniques can also be used to deposit the getter material. Preferably, the getter material is deposited by flash evaporation. Flash evaporation techniques are described in, for example, concurrently filed patent application titled "Method of Fabricating Electronic Devices" U.S. Ser. No. 10/242,068, filed September 11, 2002 ~~(attorney docket number 02P13934US)~~, which is herein incorporated by reference for all purposes.

Please replace the paragraph on page 11, line 4 with the following amended paragraph:

In one embodiment, the getter material comprises a metal, such as an alkaline earth metals, aluminum (Al), zirconium (Zr) or tantalum (Ta). Alkaline earth metals include, for example, ~~aluminum (Al),~~ magnesium (Mg), ~~zirconium (Zr),~~ calcium (Ca)~~, tantalum (Ta)~~ or barium (Ba). Preferably, the getter material comprises barium. It has been found that alkaline earth metals are constantly reactive, which prevents the formation of mechanically stable oxide films on the surface that may inhibit further sorption. The getter material may be deposited directly in the active region without packaging and separation from the device layers. This results in a reduction in device thickness, higher efficiency in the fabrication process and lower manufacturing costs. In one embodiment, mass production using roll-to-roll production (also known as "web" processing) is employed, where the getter material and other device layers are continuously or semi-continuously deposited on a flexible substrate translated between two reels.